



STP14NM65N Information



For Reference Only

Part Number STP14NM65N

Manufacturer STMicroelectronics

Category Discrete Semiconductor Products

Transistors - FETs, MOSFETs - Single

Description MOSFET N-CH 650V 12A TO-220

Package TO-220-3

For the pricing/inventory/lead time, please contact

us

Website: https://www.heisener.com E-mail: salesdept@heisener.com



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STP14NM65N Specifications

Manufacturer Part Number STPI4NM65N Manufacturer STMicroelectronics Category Discrete Semiconductor Products Transistors - FETs, MOSFETs - Single Package TO-220-3 Series MDmesh? II FET Type N-Channel Technology MOSFET (Metal Oxide) Drain to Source Voltage (Vdss) 650V Current - Continuous Drain (Id) @ 25°C 12A (Tc) Drive Voltage (Max Rds On, Min Rds On) 10V Vgs(th) (Max) @ Id 4V @ 250μA Gate Charge (Qg) (Max) @ Vgs 45nC @ 10V Input Capacitance (Ciss) (Max) @ Vds 1300pF @ 50V Vgs (Max) ±25V FET Feature - Power Dissipation (Max) 125W (Tc) Rds On (Max) @ Id, Vgs 380 mOhm @ 6A, 10V Operating Temperature 150°C (TJ) Mounting Type Through Hole Supplier Device Package TO-220AB Package / Case TO-220-3		
Category Discrete Semiconductor Products Transistors - FETs, MOSFETs - Single Package TO-220-3 Series MDmesh? II FET Type N-Channel Technology MOSFET (Metal Oxide) Parin to Source Voltage (Vdss) Current - Continuous Drain (Id) @ 25°C 12A (Tc) Drive Voltage (Max Rds On, Min Rds On) Vgs(th) (Max) @ Id Gate Charge (Qg) (Max) @ Vds 1300pF @ 50V Vgs (Max) Vgs (Max) **ET Feature** Power Dissipation (Max) Rds On (Max) @ 1d, Vgs Rds On (Max) @ Id, Vgs Rds On (Max) @ Id, Vgs Through Hole Supplier Device Package Package / Case **TO-220AB Package / Case	Manufacturer Part Number	STP14NM65N
Package TO-220-3 Series MDmesh? II FET Type N-Channel Technology MOSFET (Metal Oxide) Drain to Source Voltage (Vdss) 650V Current - Continuous Drain (Id) @ 25°C 12A (Tc) Drive Voltage (Max Rds On, Min Rds On) 10V Vgs(th) (Max) @ Id 4V @ 250μA Gate Charge (Qg) (Max) @ Vgs 45nC @ 10V Input Capacitance (Ciss) (Max) @ Vds 1300pF @ 50V Vgs (Max) ±25V FET Feature - Power Dissipation (Max) 125W (Tc) Rds On (Max) @ Id, Vgs 380 mOhm @ 6A, 10V Operating Temperature 150°C (TJ) Mounting Type Through Hole Supplier Device Package TO-220AB Package / Case TO-220-3	Manufacturer	STMicroelectronics
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FET TypeN-ChannelTechnologyMOSFET (Metal Oxide)Drain to Source Voltage (Vdss)650VCurrent - Continuous Drain (Id) @ 25°C12A (Tc)Drive Voltage (Max Rds On, Min Rds On)10VVgs(th) (Max) @ Id4V @ 250μAGate Charge (Qg) (Max) @ Vgs45nC @ 10VInput Capacitance (Ciss) (Max) @ Vds1300pF @ 50VVgs (Max)±25VFET Feature-Power Dissipation (Max)125W (Tc)Rds On (Max) @ Id, Vgs380 mOhm @ 6A, 10VOperating Temperature150°C (TJ)Mounting TypeThrough HoleSupplier Device PackageTO-220ABPackage / CaseTO-220-3	Package	TO-220-3
TechnologyMOSFET (Metal Oxide)Drain to Source Voltage (Vdss)650VCurrent - Continuous Drain (Id) @ 25°C12A (Tc)Drive Voltage (Max Rds On, Min Rds On)10VVgs(th) (Max) @ Id4V @ 250μAGate Charge (Qg) (Max) @ Vgs45nC @ 10VInput Capacitance (Ciss) (Max) @ Vds1300pF @ 50VVgs (Max)±25VFET Feature-Power Dissipation (Max)125W (Tc)Rds On (Max) @ Id, Vgs380 mOhm @ 6A, 10VOperating Temperature150°C (TJ)Mounting TypeThrough HoleSupplier Device PackageTO-220ABPackage / CaseTO-220-3	Series	MDmesh? II
Drain to Source Voltage (Vdss)650 VCurrent - Continuous Drain (Id) @ 25°C12A (Tc)Drive Voltage (Max Rds On, Min Rds On)10VVgs(th) (Max) @ Id4V @ 250μAGate Charge (Qg) (Max) @ Vgs45nC @ 10VInput Capacitance (Ciss) (Max) @ Vds1300pF @ 50VVgs (Max)±25VFET Feature-Power Dissipation (Max)125W (Tc)Rds On (Max) @ Id, Vgs380 mOhm @ 6A, 10VOperating Temperature150°C (TJ)Mounting TypeThrough HoleSupplier Device PackageTO-220ABPackage / CaseTO-220-3	FET Type	N-Channel
Current - Continuous Drain (Id) @ 25°C Drive Voltage (Max Rds On, Min Rds On) Vgs(th) (Max) @ Id Gate Charge (Qg) (Max) @ Vgs Input Capacitance (Ciss) (Max) @ Vds Vgs (Max) FET Feature Power Dissipation (Max) Rds On (Max) @ Id, Vgs 380 mOhm @ 6A, 10V Operating Temperature Mounting Type Through Hole Supplier Device Package Package / Case 12A (Tc) 150°C (10V Through Hole To-220AB TO-220AB	Technology	MOSFET (Metal Oxide)
Drive Voltage (Max Rds On, Min Rds On)10VVgs(th) (Max) @ Id4V @ 250μAGate Charge (Qg) (Max) @ Vgs45nC @ 10VInput Capacitance (Ciss) (Max) @ Vds1300pF @ 50VVgs (Max)±25VFET Feature-Power Dissipation (Max)125W (Tc)Rds On (Max) @ Id, Vgs380 mOhm @ 6A, 10VOperating Temperature150°C (TJ)Mounting TypeThrough HoleSupplier Device PackageTO-220ABPackage / CaseTO-220-3	Drain to Source Voltage (Vdss)	650V
Vgs(th) (Max) @ Id Gate Charge (Qg) (Max) @ Vgs Input Capacitance (Ciss) (Max) @ Vds Vgs (Max) FET Feature Power Dissipation (Max) Rds On (Max) @ Id, Vgs Operating Temperature 150°C (TJ) Mounting Type Supplier Device Package Package / Case 45nC @ 10V 1300pF @ 50V ±25V FET Fe 50V	Current - Continuous Drain (Id) @ 25°C	12A (Tc)
Gate Charge (Qg) (Max) @ Vgs Input Capacitance (Ciss) (Max) @ Vds 1300pF @ 50V Vgs (Max) ±25V FET Feature Power Dissipation (Max) Rds On (Max) @ Id, Vgs 380 mOhm @ 6A, 10V Operating Temperature 150°C (TJ) Mounting Type Through Hole Supplier Device Package TO-220AB Package / Case TO-220-3	Drive Voltage (Max Rds On, Min Rds On)	10V
Input Capacitance (Ciss) (Max) @ Vds Vgs (Max) EET Feature Power Dissipation (Max) Rds On (Max) @ Id, Vgs 380 mOhm @ 6A, 10V Operating Temperature 150°C (TJ) Mounting Type Through Hole Supplier Device Package TO-220AB Package / Case TO-220-3	Vgs(th) (Max) @ Id	4V @ 250μA
Vgs (Max)±25VFET Feature-Power Dissipation (Max)125W (Tc)Rds On (Max) @ Id, Vgs380 mOhm @ 6A, 10VOperating Temperature150°C (TJ)Mounting TypeThrough HoleSupplier Device PackageTO-220ABPackage / CaseTO-220-3	Gate Charge (Qg) (Max) @ Vgs	45nC @ 10V
FET Feature - Power Dissipation (Max) 125W (Tc) Rds On (Max) @ Id, Vgs 380 mOhm @ 6A, 10V Operating Temperature 150°C (TJ) Mounting Type Through Hole Supplier Device Package TO-220AB Package / Case TO-220-3	Input Capacitance (Ciss) (Max) @ Vds	1300pF @ 50V
Power Dissipation (Max) Rds On (Max) @ Id, Vgs 380 mOhm @ 6A, 10V Operating Temperature 150°C (TJ) Mounting Type Through Hole Supplier Device Package TO-220AB Package / Case TO-220-3	Vgs (Max)	±25V
Rds On (Max) @ Id, Vgs380 mOhm @ 6A, 10VOperating Temperature150°C (TJ)Mounting TypeThrough HoleSupplier Device PackageTO-220ABPackage / CaseTO-220-3	FET Feature	-
Operating Temperature 150°C (TJ) Mounting Type Through Hole Supplier Device Package TO-220AB Package / Case TO-220-3	Power Dissipation (Max)	125W (Tc)
Mounting Type Through Hole Supplier Device Package TO-220AB Package / Case TO-220-3	Rds On (Max) @ Id, Vgs	380 mOhm @ 6A, 10V
Supplier Device Package TO-220AB Package / Case TO-220-3	Operating Temperature	150°C (TJ)
Package / Case TO-220-3	Mounting Type	Through Hole
	Supplier Device Package	TO-220AB
Report errors?	Package / Case	TO-220-3
		Report errors?

STP14NM65N Guarantees



Quality Guarantees

We provide 90 days warranty. *

If the items you received were not in perfect quality, we would be responsible for your refund or replacement, but the items must be returned in their original condition.



Service Guarantees

We guarantee 100% customer satisfaction.

Our experienced sales team and tech support team back our services to satisfy all our customers.

STP14NM65N Payment Methods





















STP14NM65N Shipping Methods













If you have any question about STP14NM65N, please do not hesitate to contact us!

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